

2SA1343, 2SC3397



2018A

PNP/NPN Epitaxial Planar
Silicon Transistors

T-37-13
T-35-11

Switching Applications (with Bias Resistances $R_1=46k\Omega$, $R_2=23k\Omega$)

©1285C

Applications

- Switching circuit, inverter circuit, interface circuit, driver circuit.

Features

- Built-in bias resistor ($R_1=46k\Omega$, $R_2=23k\Omega$).
- Small-sized package (CP).

() : 2SA1343

Absolute Maximum Ratings/ $T_a=25^\circ\text{C}$

			unit
Collector to Base Voltage	V_{CB0}	(-)50	V
Collector to Emitter Voltage	V_{CEO}	(-)50	V
Emitter to Base Voltage	V_{EBO}	(-)10	V
Collector Current	I_C	(-)100	mA
Peak Collector Current	i_{cp}	(-)200	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics/ $T_a=25^\circ\text{C}$

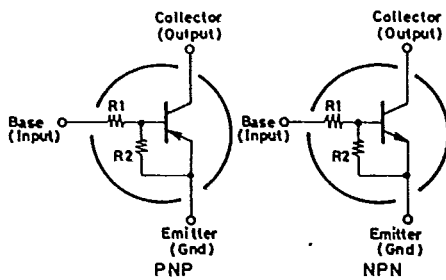
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40\text{V}, I_E=0$			(-)0.1	μA
Collector Cutoff Current	I_{CEO}	$V_{CE}=(-)40\text{V}, I_B=0$			(-)0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5\text{V}, I_C=0$	(-)40	(-)72	(-)100	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)5\text{V}, I_C=(-)5\text{mA}$	50			
Gain Band-width product	f_T	$V_{CE}=(-)10\text{V}, I_C=(-)5\text{mA}$		250 (200)		MHz
Output Capacitance	c_{ob}	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$		3.5 (5.3)		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)5\text{mA}, I_B=(-)0.25\text{mA}$	(-)0.1	(-)0.3		V

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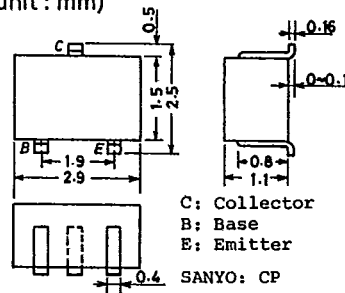
Marking

2SA1343: DL, 2SC3397: DY

Electrical Connection



Case Outline 2018A (unit : mm)



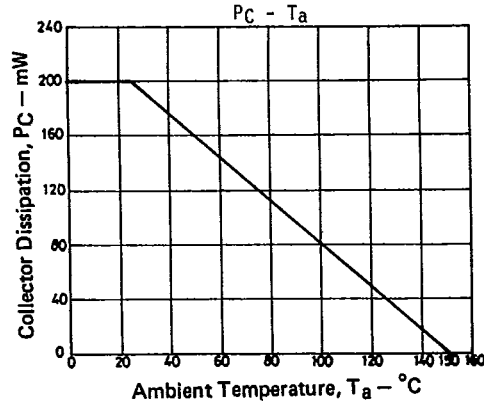
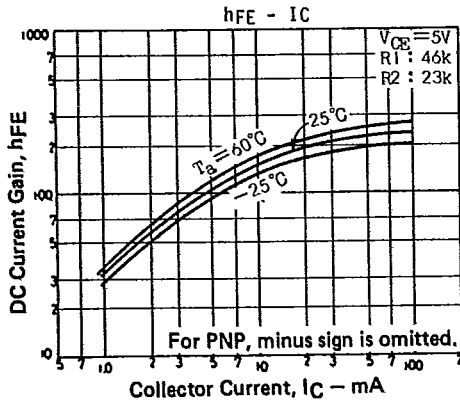
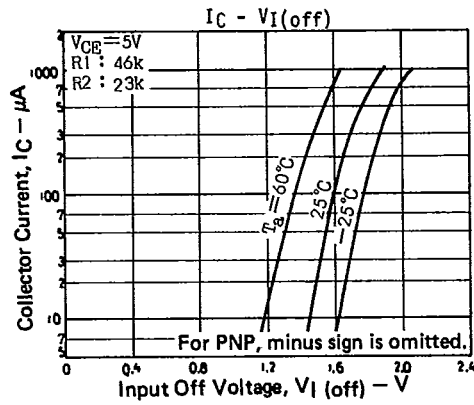
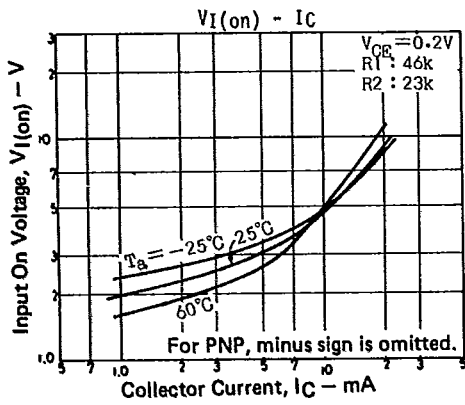
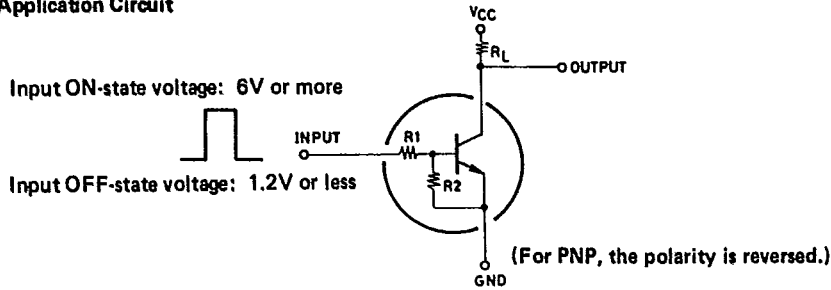
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			min	typ	max	unit
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)50			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)100\mu A, R_{BE} = \infty$	(-)50			V
Input Off Voltage	$V_{I(off)}$	$V_{CE} = (-)5V, I_C = (-)100\mu A$	(-)1.2	(-)1.6	(-)2.3	V
Input On Voltage	$V_{I(on)}$	$V_{CE} = (-)0.2V, I_C = (-)5mA$	(-)1.5	(-)3.1	(-)6.0	V
Input Resistance	R1		32	46	60	k Ω
Input Resistance Ratio	R1/R2		1.8	2.0	2.2	-

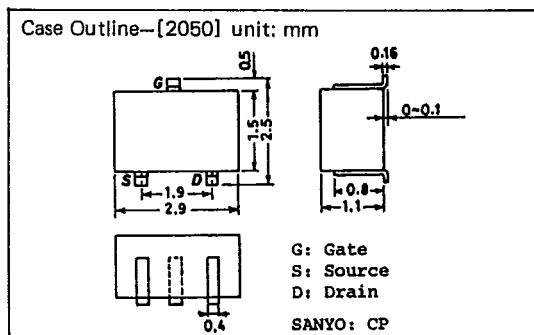
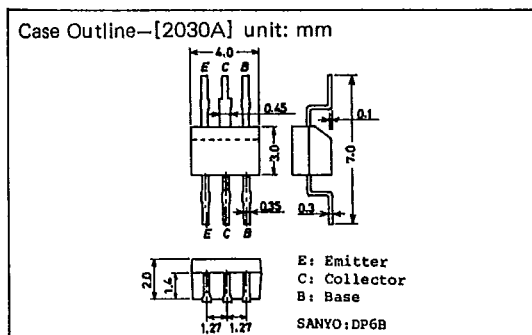
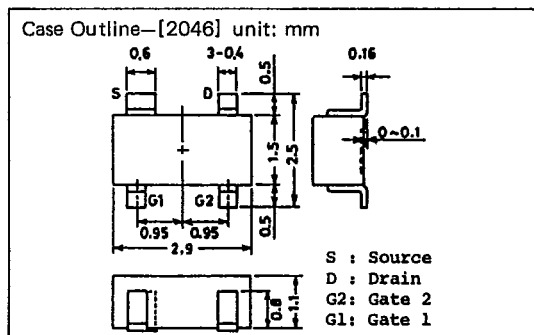
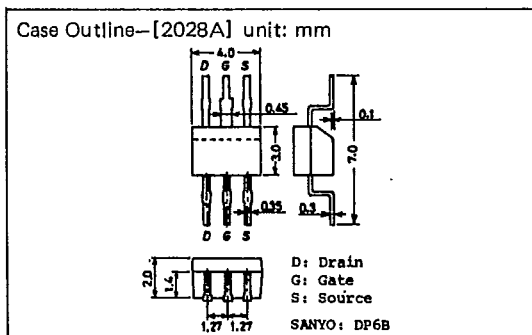
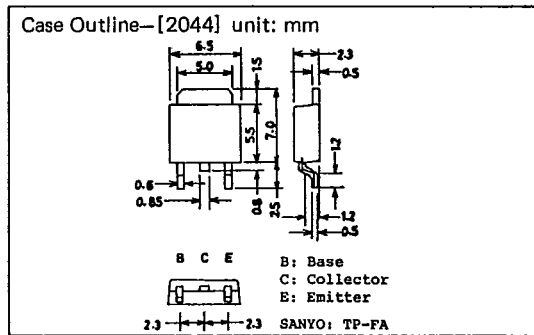
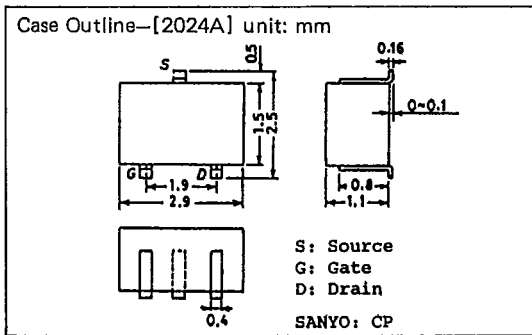
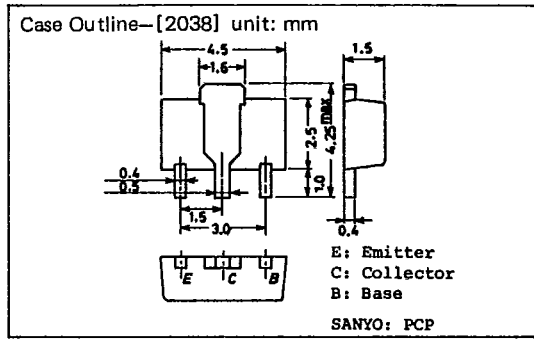
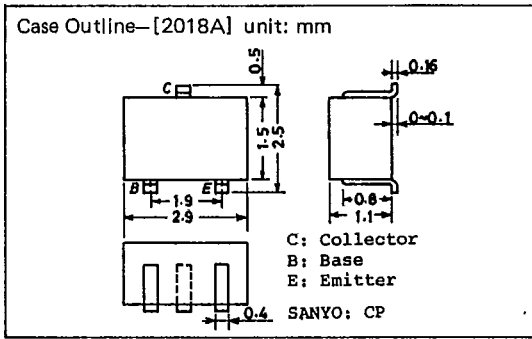
■ Sample Application Circuit



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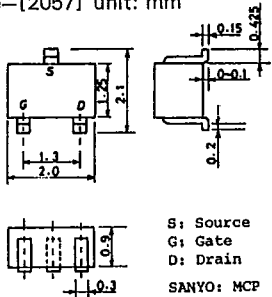
CASE OUTLINES OF SURFACE MOUNT TRANSISTORS

- All of Sanyo surface mount transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.



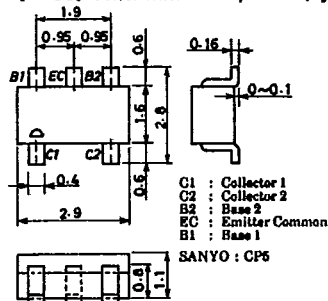
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Case Outline—[2057] unit: mm



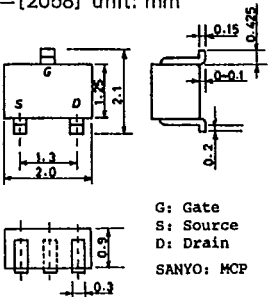
S: Source
G: Gate
D: Drain
SANYO: MCP

Case Outline—[2066] unit: mm



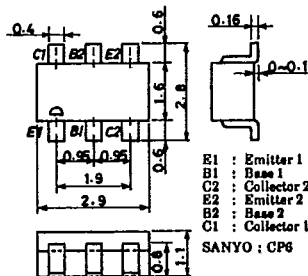
C1: Collector 1
C2: Collector 2
B2: Base 2
EC: Emitter Common
B1: Base 1
SANYO: CP6

Case Outline—[2058] unit: mm



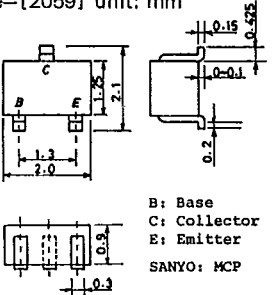
G: Gate
S: Source
D: Drain
SANYO: MCP

Case Outline—[2067] unit: mm



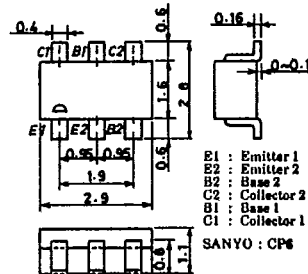
E1: Emitter 1
B1: Base 1
C2: Collector 2
E2: Emitter 2
B2: Base 2
C1: Collector 1
SANYO: CP6

Case Outline—[2059] unit: mm



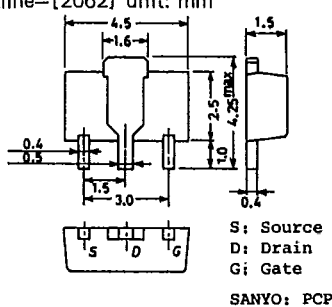
B: Base
C: Collector
E: Emitter
SANYO: MCP

Case Outline—[2068] unit: mm



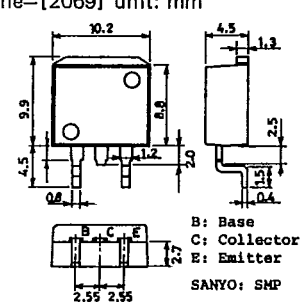
B1: Emitter 1
E2: Emitter 2
B2: Base 2
C2: Collector 2
B1: Base 1
C1: Collector 1
SANYO: CP6

Case Outline—[2062] unit: mm



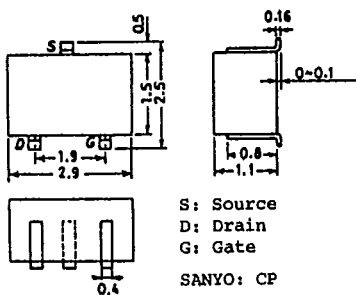
S: Source
D: Drain
G: Gate
SANYO: PCP

Case Outline—[2069] unit: mm



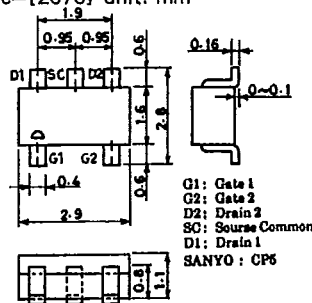
B: Base
C: Collector
E: Emitter
SANYO: SMP

Case Outline—[2065] unit: mm



S: Source
D: Drain
G: Gate
SANYO: CP

Case Outline—[2070] unit: mm



G1: Gate 1
G2: Gate 2
D2: Drain 2
SC: Source Common
D1: Drain 1
SANYO: CP6

T-9120

